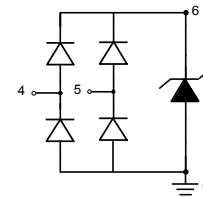
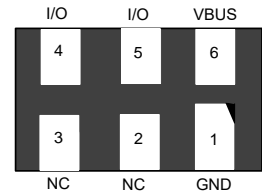


Features

- 50Watts peak pulse power ($T_P = 8/20\mu s$)
- DFN1109-6 package
- Protect up to 2-lines
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Ultra low capacitance (0.2pF typical I/O to I/O)
- ESD Protection for high-speed data lines to:
IEC 61000-4-2 $\pm 8kV$ contact $\pm 15kV$ air
IEC 61000-4-4 (EFT) 40A (5/50ns)
IEC 61000-4-5 (Lightning) 3A (8/20 μs)



Mechanical Data

- **Case:** DFN1109-6 (plastic package).
Lead free; RoHS compliant; Halogen free
- **Molding Compound Flammability Rating:**
UL 94 V-0
- **Terminals:** High temperature soldering guaranteed:
260 °C/10 sec. at terminals

Applications

- USB 2.0
- MMC Port
- Video Port
- Digital Visual Interface (DVI)
- High speed serial interfaces

Absolute Maximum Ratings

Ratings at 25 °C, ambient temperature unless otherwise specified

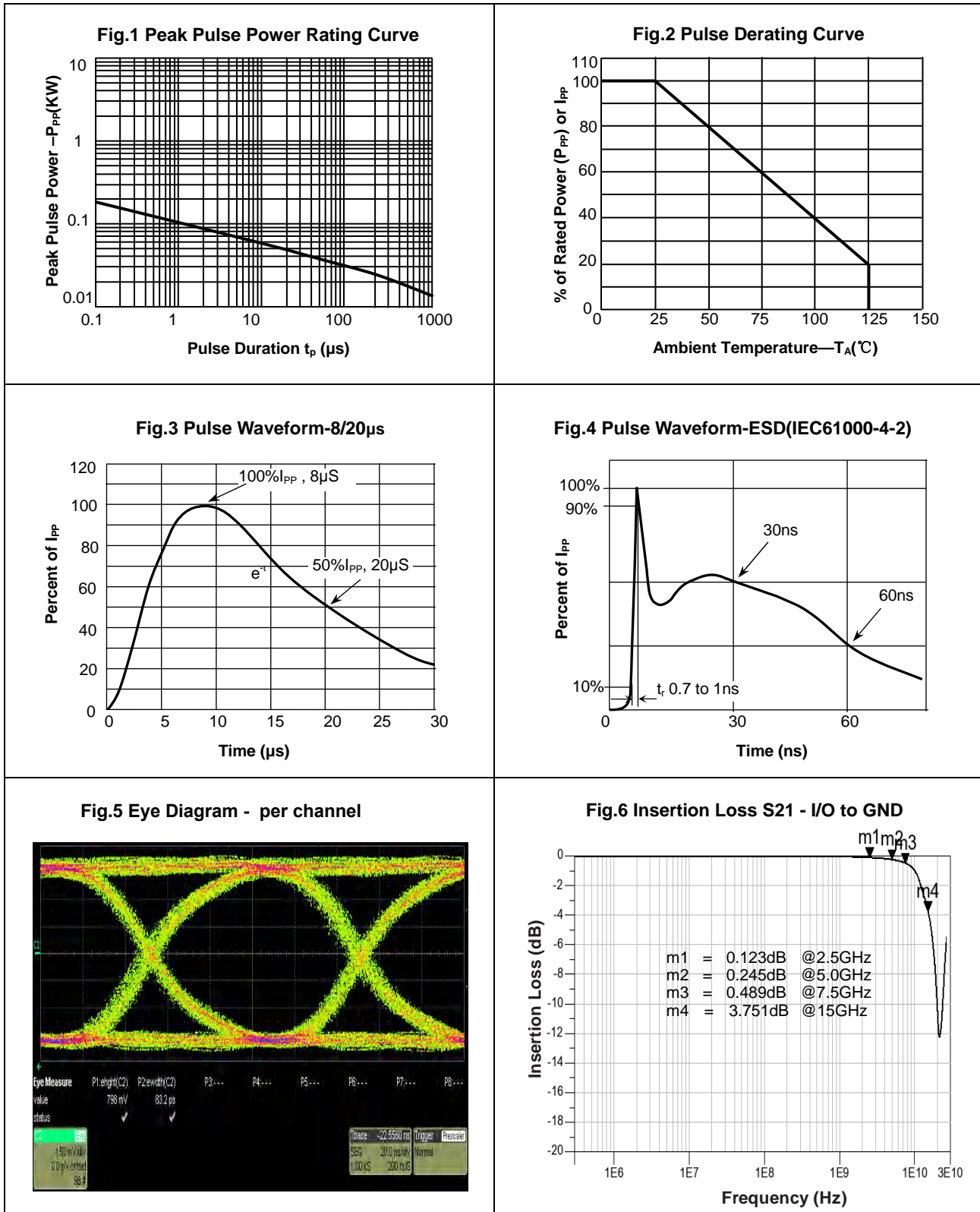
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_P=8/20\mu s$)	P_{PP}	50	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	8/15	kV
Peak Pulse Current ($T_P = 8/20\mu s$)	I_{PP}	3.0	A
Junction Temperature	T_J	-55 to +125	°C
Storage temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

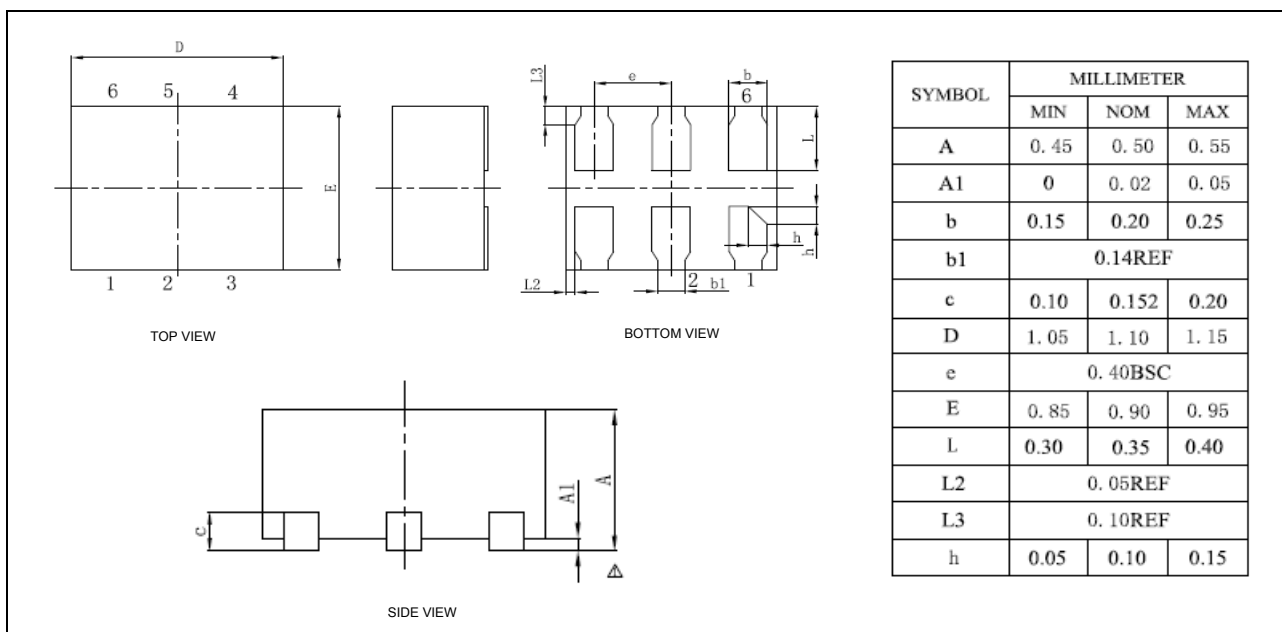
($T_A = 25\text{ °C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}	Pin6 to GND			6.5	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6.0	8.5		V
Reverse Leakage Current	I_R	$V_R=5V$		0.1	0.5	μA
Clamping Voltage(SURGE)	V_C	$I_{PP}=3A, T_P=8/20\mu s$			18.5	V
Clamping Voltage(ESD)	V_C	$V_{ESD} = +8kV$		15		V
Junction Capacitance	C_J	$V_R=0V, f=1MHz, I/O$ to I/O		0.2		pF
	C_J	$V_R=0V, f=1MHz, I/O$ to GND		0.2		pF

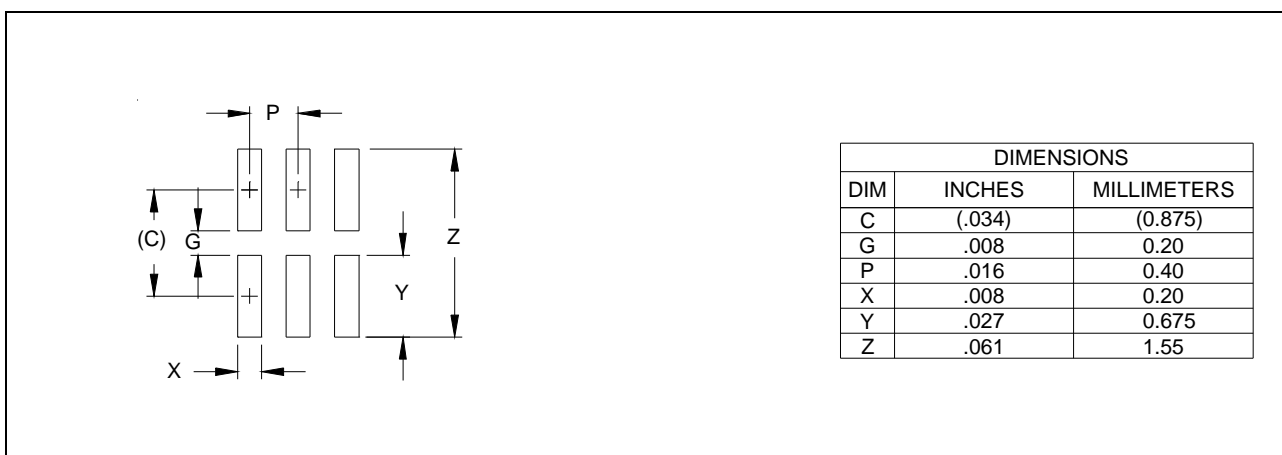
Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)



Package Dimensions



Pad Dimensions



Ordering information

Order code	Marking	Package	Packaging option	Base quantity	Packaging specification
YEU11J66R03AV	52N	DFN1109-6	Tape and reel	3000pcs / reel	EIA STD RS-481